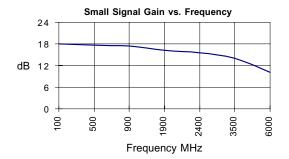




Product Description

Stanford Microdevices' SGA-2363 is a high performance cascadeable 50-ohm amplifier designed for operation from a 2.7-volt supply. This RFIC uses the latest Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process featuring 1 micron emitters with F_T up to 50 GHz.

This circuit uses a darlington pair topology with resistive feedback for broadband performance as well as stability over its entire temperature range. Internally matched to 50 ohm impedance, the SGA-2363 requires only DC blocking and bypass capacitors for external components.



SGA-2363

DC-2800 MHz Silicon Germanium HBT Cascadeable Gain Block



Product Features

- DC-2800 MHz Operation
- 2.7V Single Voltage Supply
- High Output Intercept: +20.0dBm typ. at 850 MHz
- Low Noise Figure: 2.9 dB typ. at 850 MHz

Applications

- Broadband Gain Blocks
- Cordless Phones
- IF/ RF Buffer Amplifier
- Drivers for CATV Amplifiers

Symbol	Parameters: Test Conditions: Z ₀ = 50 Ohms, Id = 20 mA, T = 25°C		Units	Min.	Тур.	Max.
P _{1dB}	Output Power at 1dB Compression	f = 850 MHz f = 1950 MHz	dBm dBm		8.2 7.2	
S ₂₁	Small Signal Gain	f = DC - 1000 MHz f = 1000 - 2000 MHz f = 2000 - 2800 MHz	dB dB dB	15.7	17.5 16.7 15.5	
S ₁₂	Reverse Isolation	f = DC - 1000 MHz f = 1000 - 2000 MHz f = 2000 - 2800 MHz	dB dB dB		20.9 21.3 21.2	
S ₁₁	Input VSWR	f = DC - 2000 MHz f = 2400 - 2800 MHz	-		1.4:1 1.5:1	
S ₂₂	Output VSWR	f = DC - 2000 MHz f = 2000 - 2800 MHz	-		1.3:1 1.2:1	
IP ₃	Third Order Intercept Point Power out per Tone = -10 dBm	f = 850 MHz f = 1950 MHz	dBm dBm		19.4 20.4	
NF	Noise Figure	f = DC - 1000 MHz f = 1000 - 2400 MHz	dB dB		2.9 3.4	
T _D	Group Delay	f = 1000 MHz	pS		107	
V _D	Device Voltage		V	2.4	2.7	3.0

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Phone: (800) SMI-MMIC



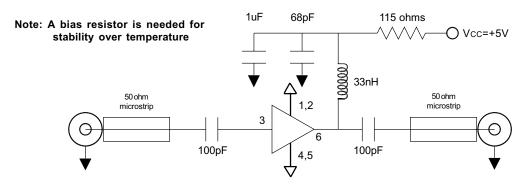


Specification					Test
Parameter	Min	Тур.	Max.	Unit	Condition
Bandwidth					T= 25C
Frequency Range	DC		2800	MHz	
Device Bias					T= 25C
Operating Voltage		2.7		V	
Operating Current		20		mA	
500 MHz					T= 25C
Gain		17.7		dB	
Noise Figure		2.9		dB	
Output IP3		20.5		dBm	
Output P1dB		8.2		dBm	
Input Return Loss		16.4		dB	
Isolation		21.3		dB	
850 MHz					T= 25C
Gain		17.4		dB	
Noise Figure		2.9		dB	
Output IP3		19.4		dBm	
Output P1dB		8.2		dBm	
Input Return Loss		15.7		dB	
Isolation		21.3		dB	
1950 MHz					T= 25C
Gain		16.1		dB	
Noise Figure		3.3		dB	
Output IP3		20.4		dBm	
Output P1dB		7.2		dBm	
Input Return Loss		13.3		dB	
Isolation		21.6		dB	
2400 MHz					T= 25C
Gain		15.6		dB	
Noise Figure		3.6		dB	
Output IP3		19.2		dBm	
Output P1dB		6.8		dBm	
Input Return Loss		12.3		dB	
Isolation		21.6		dB	

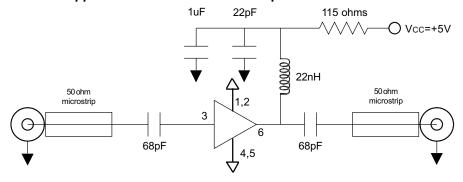


Pin #	Function	Description	Device Schematic
1	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.	
2	GND	Sames as Pin 1	
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
4	GND	Sames as Pin 1	
5	GND	Sames as Pin 1	
6	RF OUT	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.	

Application Schematic for +5V Operation at 900 MHz

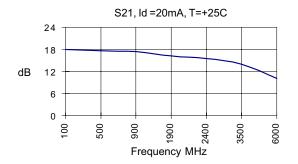


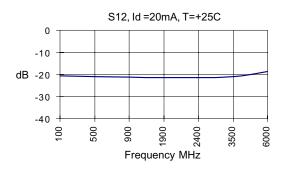
Application Schematic for +5V Operation at 1900 MHz

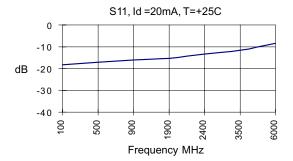


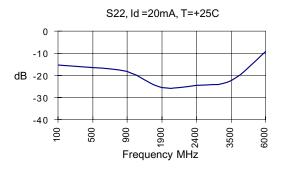


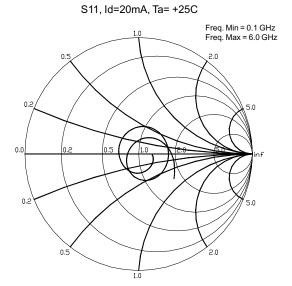


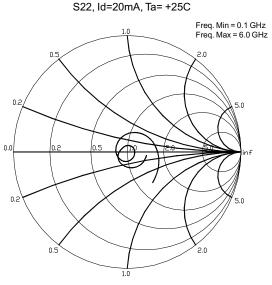






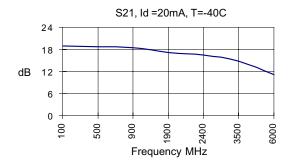


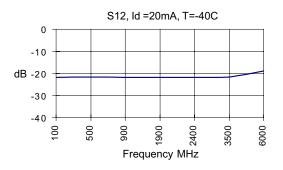


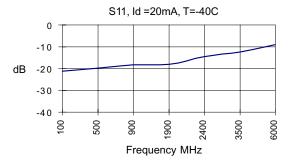


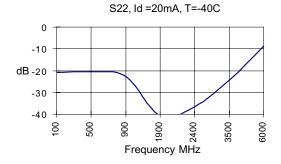


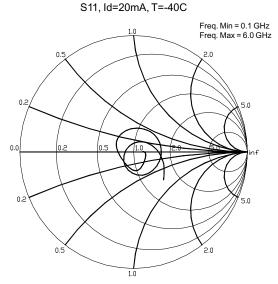


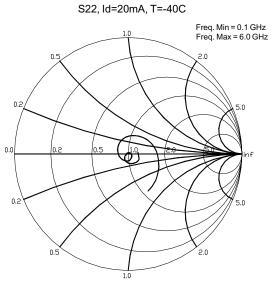






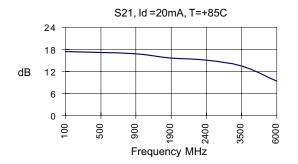


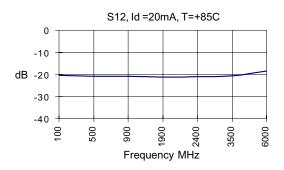


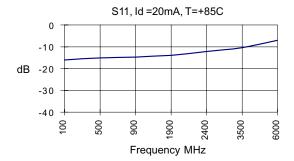


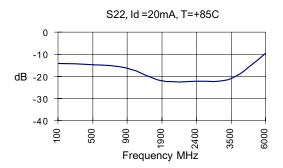


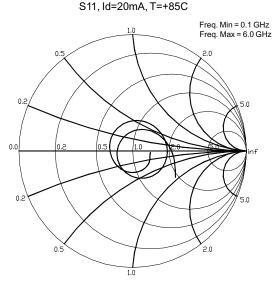


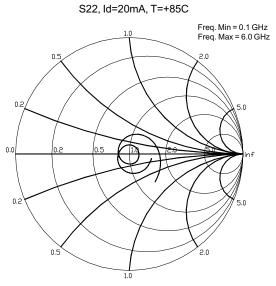
















Absolute Maximum Ratings

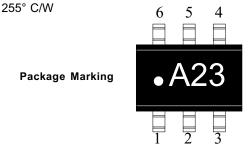
Parameter	Value	Unit
Supply Current	40	mA
Operating Temperature	-40 to +85	С
Maximum Input Power	+3	dBm
Storage Temperature Range	-40 to +85	C
Operating Junction Temperature	+125	С

Caution:



Operation of this device above any one of these parameters may cause permanent damage. Appropriate precautions in handling, packaging and testing devices must be observed.

Thermal Resistance (Lead-Junction):



Part Number Ordering Information

SGA-2363 DC-2800 MHz 2.7V SiGe Amplifier

Part Number	Reel Size	Devices/Reel	
SGA-2363-TR1	7"	3000	

Recommended Bias Resistor Values					
Supply Voltage(Vs)	3V	5V	7.5V	9V	12V
Rbias (Ohms)	15	115	240	315	465

Pad Layout

Pin Designation				
1	GND			
2	GND			
3	RF in			
4	GND			
5	GND			
6	RF out			

Note: Pin 1 is on lower left when you can read package marking

Package Dimensions

